

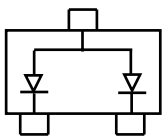
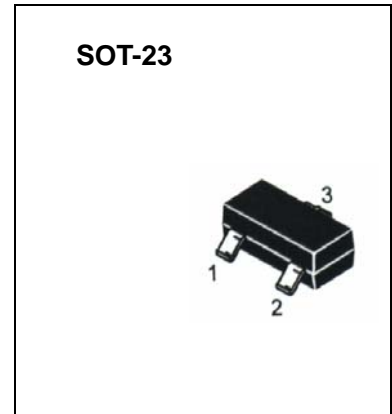


SOT-23 Plastic-Encapsulate Diodes

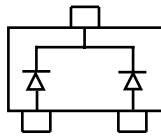
BAW56/BAV70/BAV99 SWITCHING DIODE

FEATURES

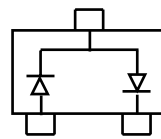
- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



BAW56 Marking: A1



BAV70 Marking: A4



BAV99 Marking: A7

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Reverse voltage	V _R	70	V
Forward Current	I _F	200	mA
Peak Forward Surge Current	I _{FM(surge)}	500	mA
Power Dissipation	P _D	225	mW
Thermal Resistance Junction to Ambient Air	R _{θJA}	556	°C/W
Junction temperature	T _J	150	°C
Storage temperature range	T _{STG}	-55-150	°C

Electrical Characteristics @T_A=25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _R	70			V	I _R =100μA
Forward voltage	V _{F1}			0.715	V	I _F =1mA
	V _{F2}			0.855	V	I _F =10mA
	V _{F3}			1	V	I _F =50mA
	V _{F4}			1.25	V	I _F =150mA
Reverse current	I _R			2.5	μA	V _R =70V
Capacitance between terminals	C _T			1.5	pF	V _R =0, f=1MHz
Reverse recovery time	t _{rr}			6	ns	I _F = I _R = 10mA, I _{rr} = 0.1 x I _R , R _L = 100Ω

Typical Characteristics

BAW56/BAV70/BAV99

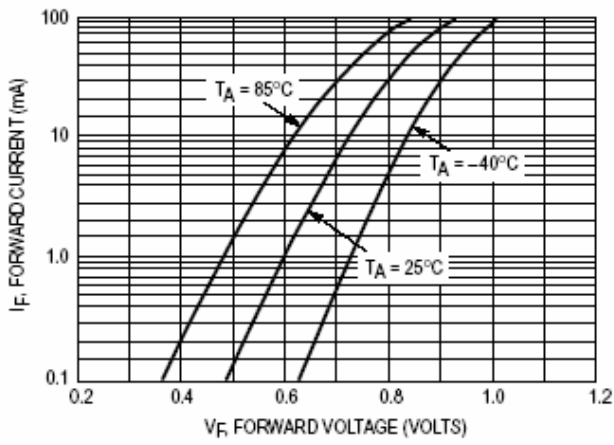


Figure 1. Forward Voltage

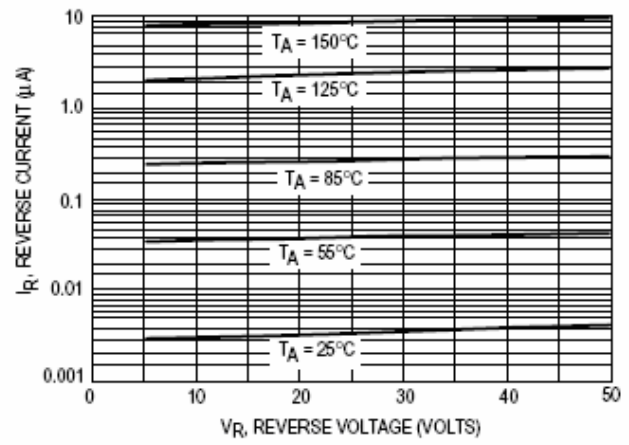


Figure 2. Leakage Current

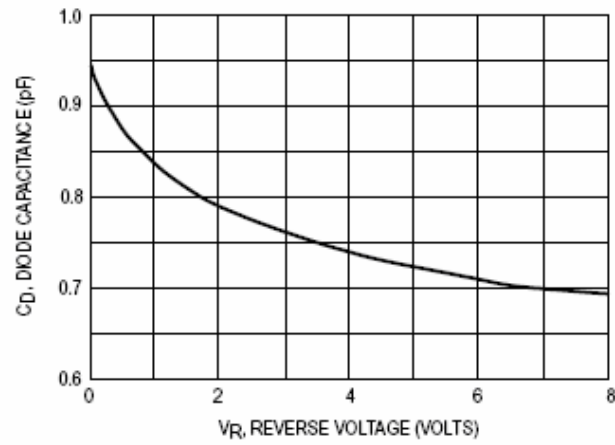


Figure 3. Capacitance